

## N-channel 600 V, 0.135 $\Omega$ typ., 20 A MDmesh™ II Power MOSFET in a TO-220FP package

Datasheet - production data

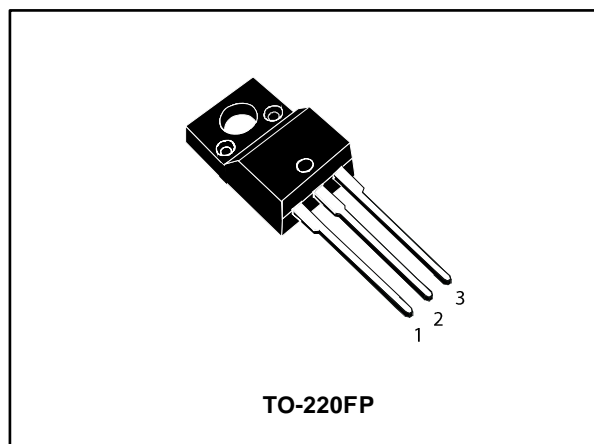
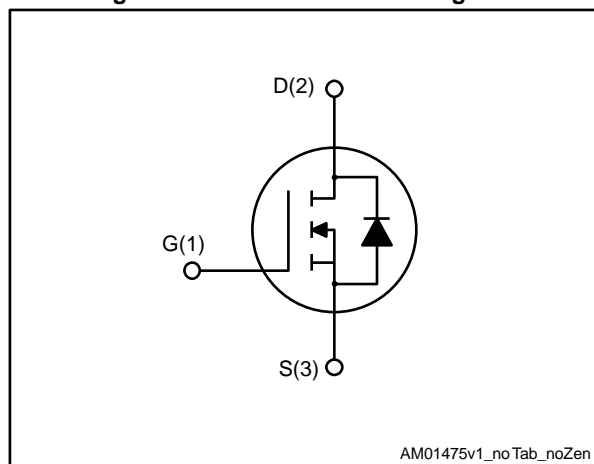


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STF26NM60N	600 V	0.165 $\Omega$	20 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packaging
STF26NM60N	26NM60N	TO-220FP	Tube

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## Contents

<b>1</b>	<b>Electrical ratings .....</b>	<b>3</b>
<b>2</b>	<b>Electrical characteristics .....</b>	<b>4</b>
	2.1 Electrical characteristics (curves).....	6
<b>3</b>	<b>Test circuits .....</b>	<b>8</b>
<b>4</b>	<b>Package information .....</b>	<b>9</b>
	4.1 TO-220FP package information .....	10
<b>5</b>	<b>Revision history .....</b>	<b>12</b>

# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	600	V
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ °C}$	20	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ °C}$	12.6	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	80	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	35	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ ; $T_C = 25\text{ °C}$ )	2500	V
$T_{stg}$	Storage temperature range	-55 to 150	°C
$T_j$	Operating junction temperature range		

**Notes:**

(1)Limited by package.

(2)Pulse width limited by safe operating area.

(3) $I_{SD} \leq 20\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} \leq V_{(BR)DSS}$ ,  $V_{DD} \leq 80\% V_{(BR)DSS}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	3.6	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	°C/W

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AS}$	Single pulse avalanche current (pulse width limited by $T_{jmax}$ )	6	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J=25\text{ °C}$ , $I_D=I_{AR}$ , $V_{DD}=50\text{ V}$ )	610	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5: On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}$ <sup>(1)</sup>			100	
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 0.1$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$		0.135	0.165	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	1800	-	pF
$C_{oss}$	Output capacitance		-	115	-	pF
$C_{riss}$	Reverse transfer capacitance		-	6	-	pF
$C_{oss\text{ eq.}}$ <sup>(1)</sup>	Equivalent output capacitance	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ to }480\text{ V}$	-	310	-	pF
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14: "Test circuit for gate charge behavior"</a> )	-	60	-	nC
$Q_{gs}$	Gate-source charge		-	8.5	-	nC
$Q_{gd}$	Gate-drain charge		-	30	-	nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	2.8	-	$\Omega$

**Notes:**

<sup>(1)</sup> $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DS}$

**Table 7: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 10\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 18: "Switching time waveform"</a> )	-	13	-	ns
$t_r$	Rise time		-	25	-	ns
$t_{d(off)}$	Turn-off delay time		-	85	-	ns
$t_f$	Fall time		-	50	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		20	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD} = 20 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	370		ns
$Q_{rr}$	Reverse recovery charge		-	5.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	31.6		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 20 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	450		ns
$Q_{rr}$	Reverse recovery charge		-	7.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	32.5		A

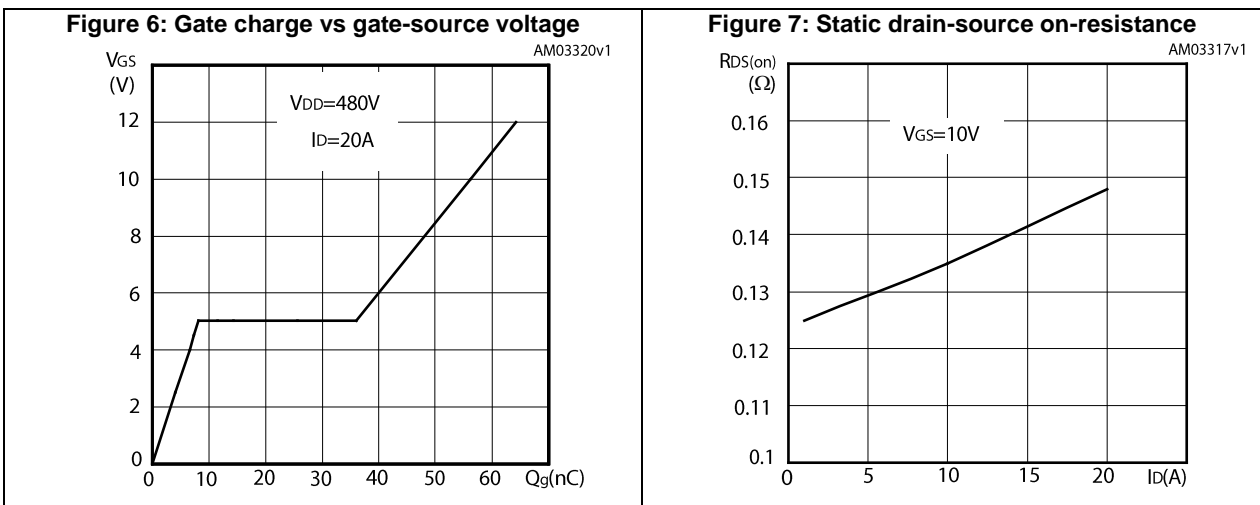
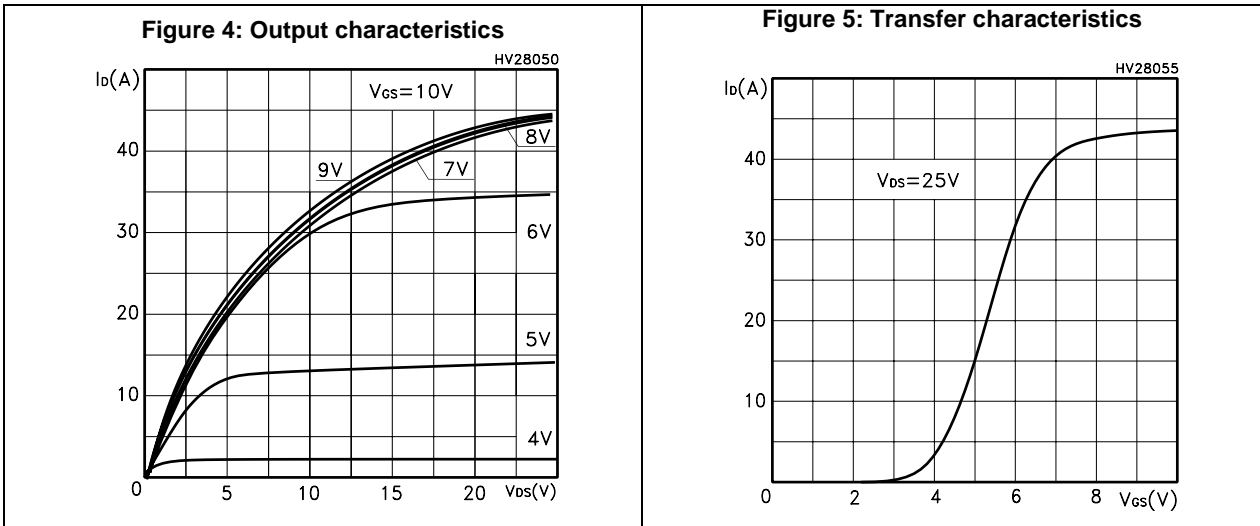
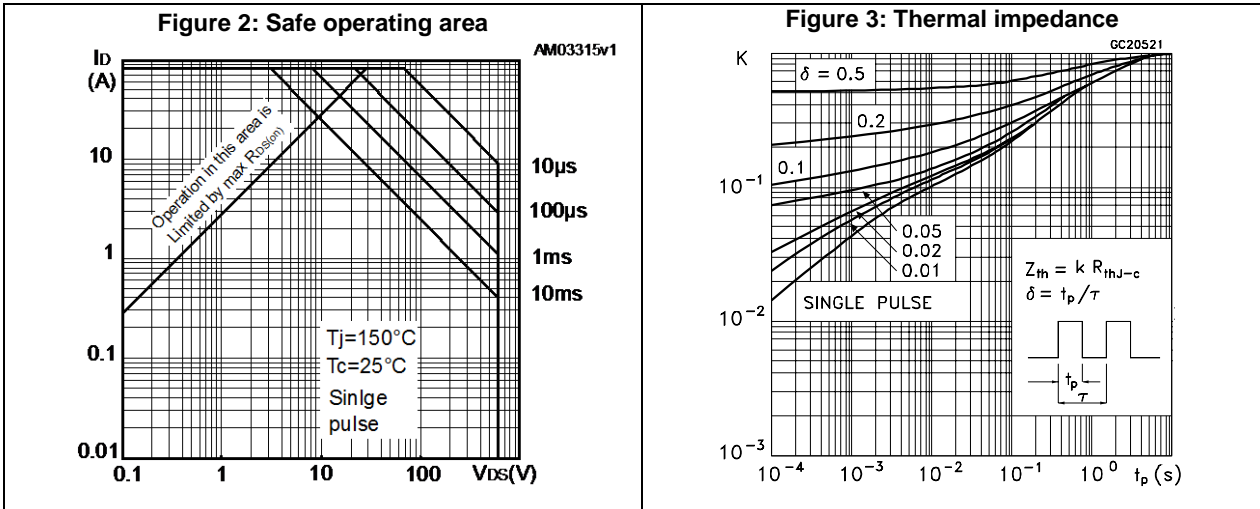
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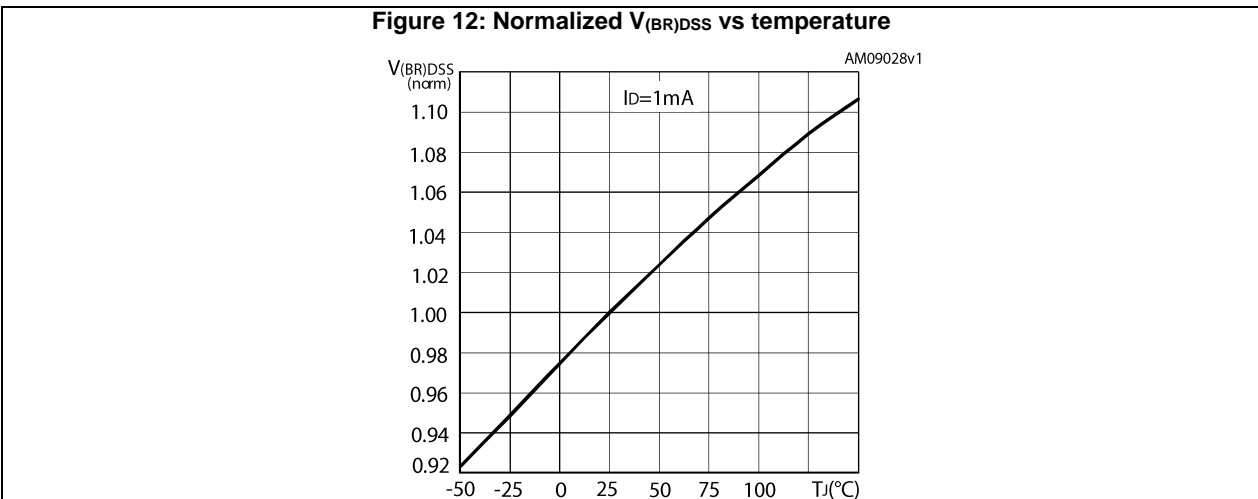
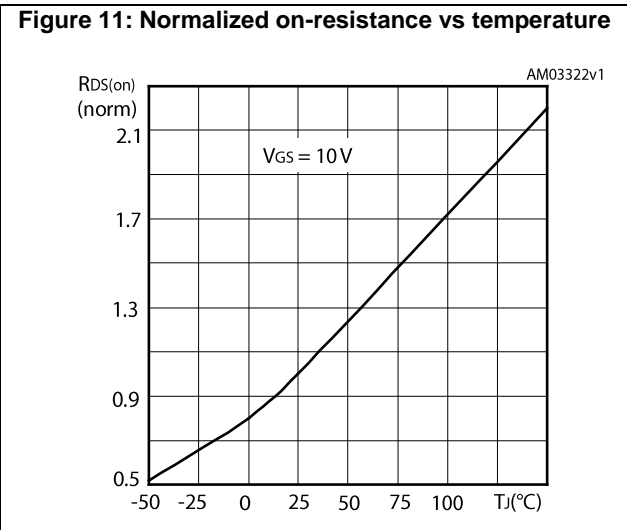
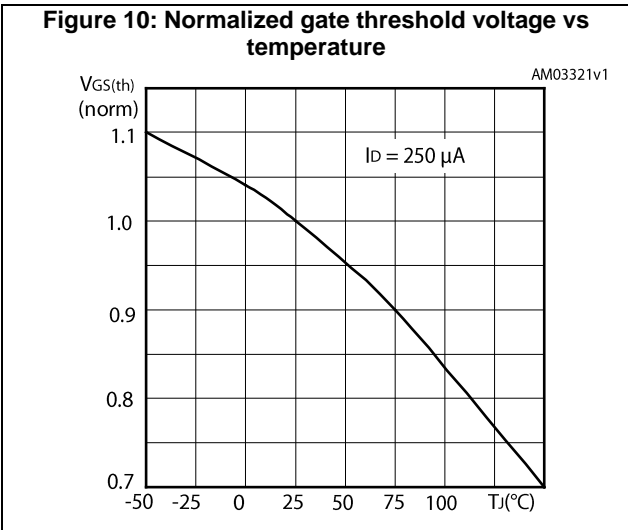
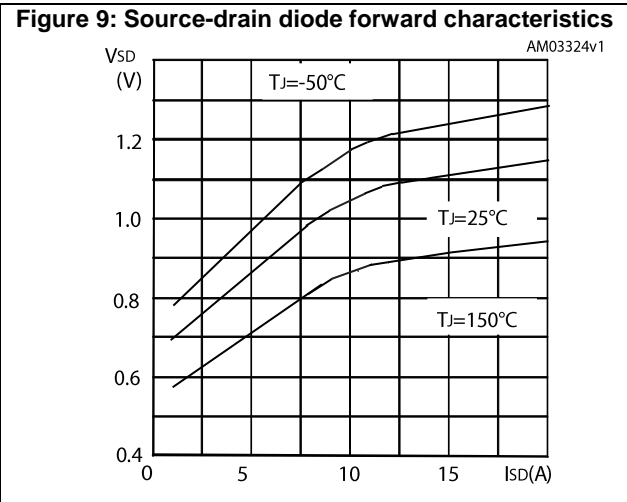
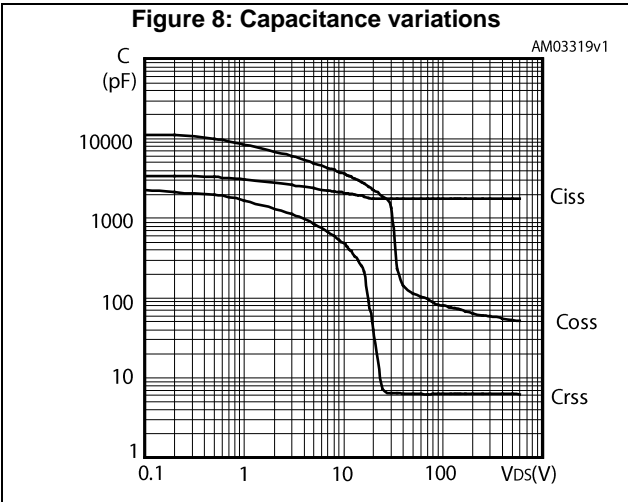
(1) Pulse width limited by package.

(2) Pulse width limited by safe operating area.

(3) Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)





### 3 Test circuits

**Figure 13: Test circuit for resistive load switching times**



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**Figure 14: Test circuit for gate charge behavior**



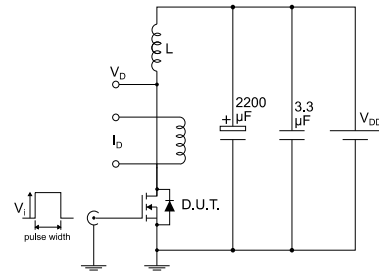
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**Figure 15: Test circuit for inductive load switching and diode recovery times**



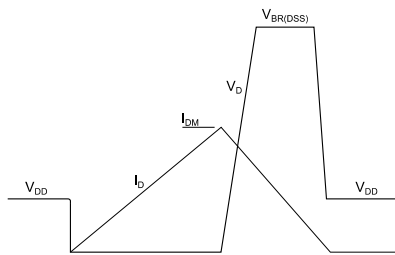
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**Figure 16: Unclamped inductive load test circuit**



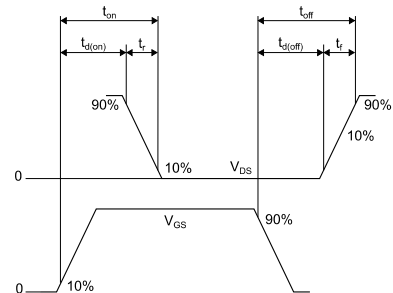
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**Figure 17: Unclamped inductive waveform**



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**Figure 18: Switching time waveform**



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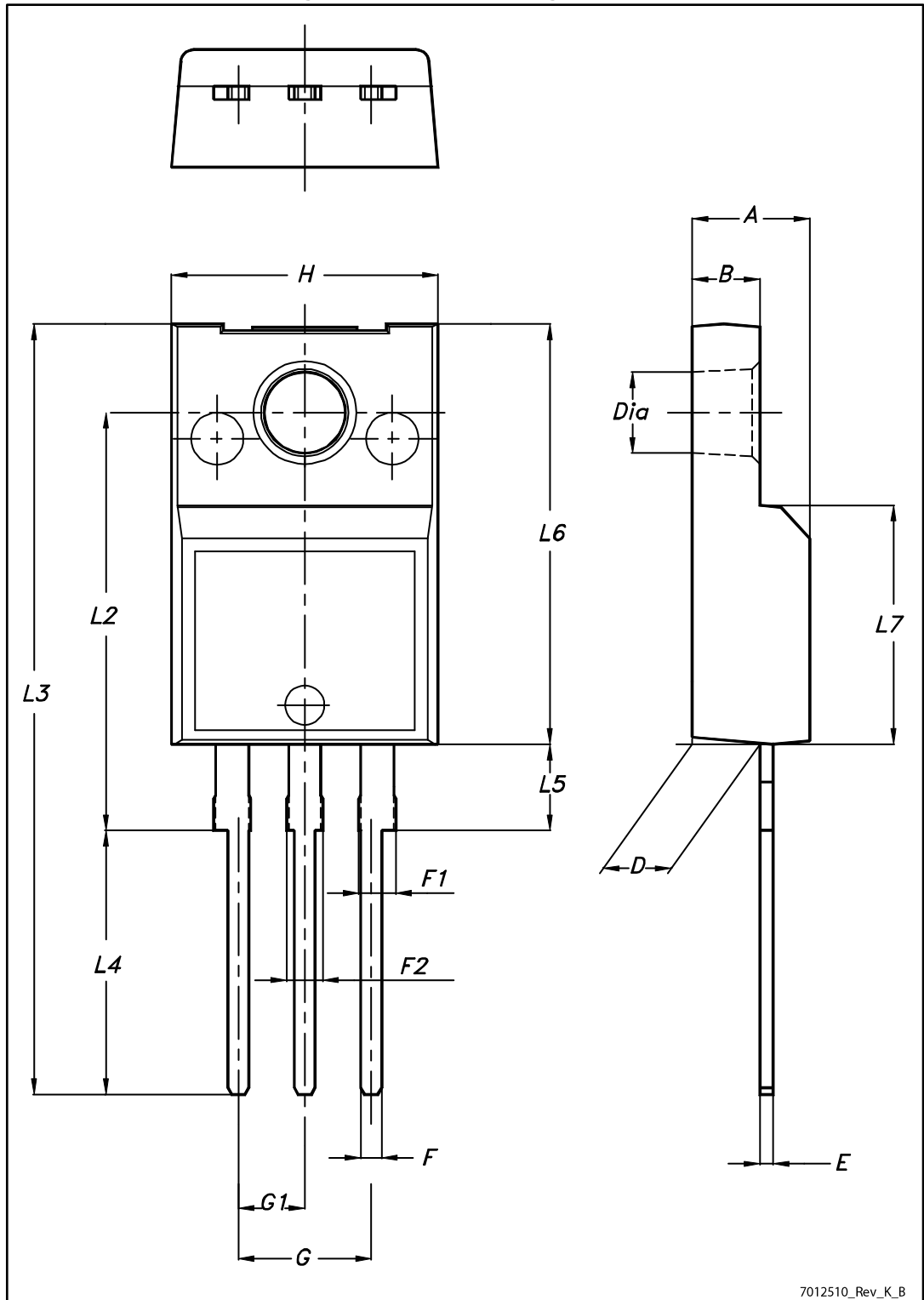


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-220FP package information

Figure 19: TO-220FP package outline



7012510\_Rev\_K\_B

Table 9: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

## 5 Revision history

Table 10: Document revision history

Date	Revision	Changes
13-Dec-2016	1	First release. Part number previously included in datasheet DocID15642

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